

ABSTRACT

Provided is a copper anode or a phosphorous-containing copper anode for use in performing electroplating copper on a semiconductor wafer, wherein
5 purity of the copper anode or the phosphorous-containing copper anode excluding phosphorous is 99.99wt% or higher, and silicon as an impurity is 10wtppm or less. Additionally provided is an electroplating copper method capable of effectively preventing the adhesion of particles on a plating object, particularly onto a semiconductor wafer during electroplating copper, a
10 phosphorous-containing copper anode for use in such electroplating copper, and a semiconductor wafer comprising a copper layer with low particle adhesion formed by the foregoing copper electroplating.